

IN THE CLAIMS

Please amend the claims as follows:

31 21. (New) The trench capacitor as recited in claim 18, wherein the crystalline nitride layer is between 2 and 6 atoms thick.

22. (New) The trench capacitor as recited in claim 18, wherein the crystalline nitride layer includes stoichiometric Si_3N_4 .

Sub C17 23. (New) A trench capacitor comprising:

a crystalline silicon substrate including a trench having a surface formed in the substrate, the surface being substantially free of native oxide;

a crystalline silicon nitride layer, formed on the surface of the trench; and
an amorphous silicon nitride layer formed on the crystalline silicon nitride layer, the crystalline silicon nitride layer and the amorphous silicon nitride layer for forming a dielectric between electrodes.

24. (New) The trench capacitor as recited in claim 23, wherein the crystalline silicon nitride layer includes a thickness of between about 3 Å and about 40 Å.

25. (New) The trench capacitor as recited in claim 23, wherein the amorphous nitride layer is oxidized.